NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE2333Y uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

• $V_{DS} = -12V, I_{D} = -6A$

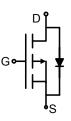
 $R_{DS(ON)} < 45 \text{m}\Omega(\text{max}) @ V_{GS} = -2.5 \text{V}$

 $R_{DS(ON)} < 30 m\Omega(max) @ V_{GS} = -4.5 V$

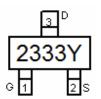
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT-23-3L top view

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2333Y	NCE2333Y	SOT-23-3L	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (TA=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	-12	V	
Gate-Source Voltage	V _{GS}	±12	V	
Drain Current -Continuous	I _D	-6	Α	
Drain Current -Pulsed (Note 1)	I _{DM}	-20	А	
Maximum Power Dissipation	P _D	1.8	W	
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$	

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	69	°C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-12	-	-	V



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NCE2333Y

Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-12V,V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V		-	±100	nA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =-250μA	-0.4	-0.65	-1.0	V
Davis Course On Otata Basistana	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-6A	-	19	30	mΩ
Drain-Source On-State Resistance		V _{GS} =-2.5V, I _D =-5A	-	26	45	
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-6A		17	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss}	\/ - C\/\/ -O\/	-	1100	-	PF
Output Capacitance	C _{oss}	V_{DS} =-6V, V_{GS} =0V, F=1.0MHz	-	390	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0IVID2	-	300	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	25	-	nS
Turn-on Rise Time	t _r	V_{DD} =-6 V , I_{D} =-1 A ,	-	45	-	nS
Turn-Off Delay Time	t _{d(off)}	R_L =6 Ω , V_{GEN} =-4.5 V , R_g =6 Ω	-	72	-	nS
Turn-Off Fall Time	t _f		-	60	-	nS
Total Gate Charge	Qg		-	11.5	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =-6V, I_{D} =-6A, V_{GS} =-4.5V	-	1.5	-	nC
Gate-Drain Charge	Q_{gd}		-	3.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-1.0A	-	-	-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-6	Α

Notes:

- $\textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature.}$
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

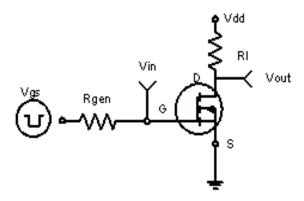


Figure 1:Switching Test Circuit

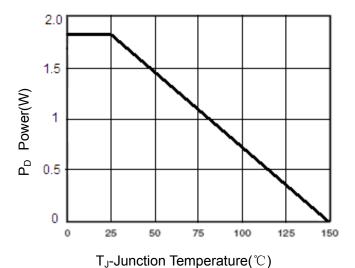


Figure 3 Power Dissipation

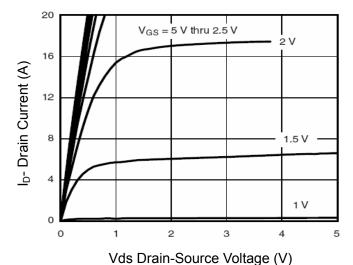


Figure 5 Output Characteristics

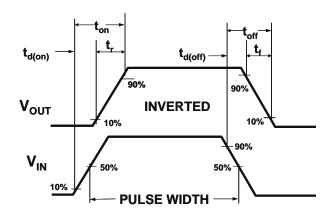
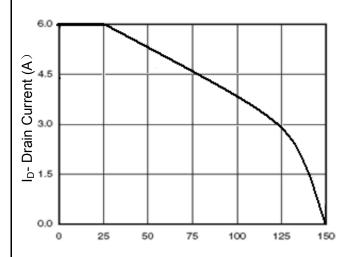


Figure 2:Switching Waveforms



T_J-Junction Temperature(°C)

Figure 4 Drain Current

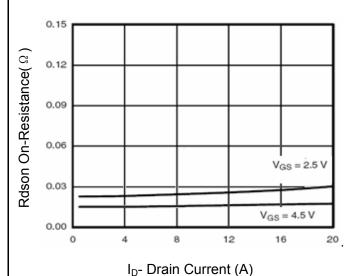
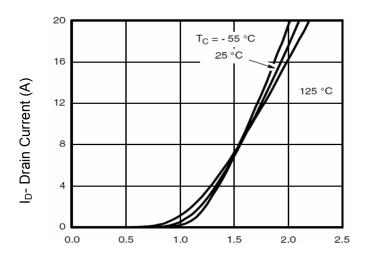
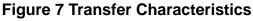


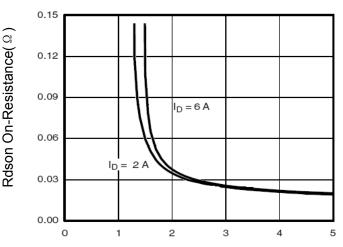
Figure 6 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)





Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

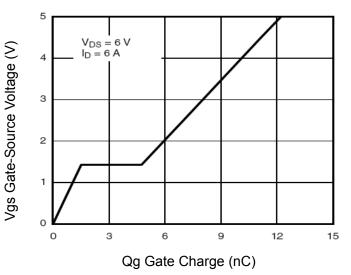
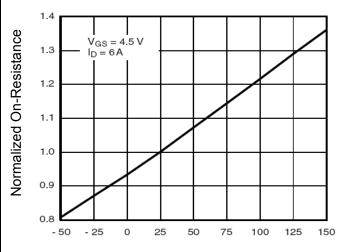
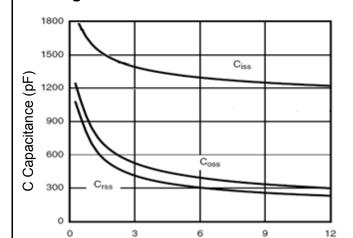


Figure 11 Gate Charge



 T_J -Junction Temperature($^{\circ}$ C)

Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds

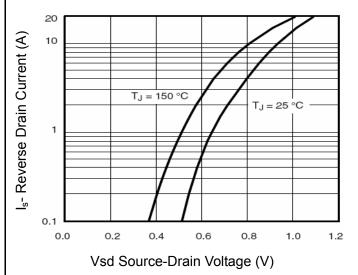
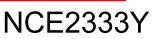
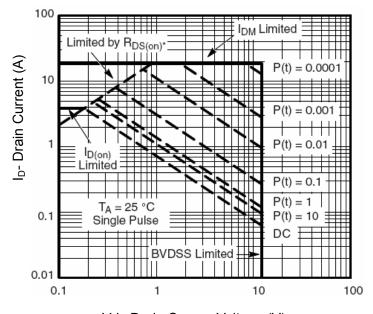


Figure 12 Source- Drain Diode Forward

Pb Free Product





Vds Drain-Source Voltage (V)

Figure 13 Safe Operation Area

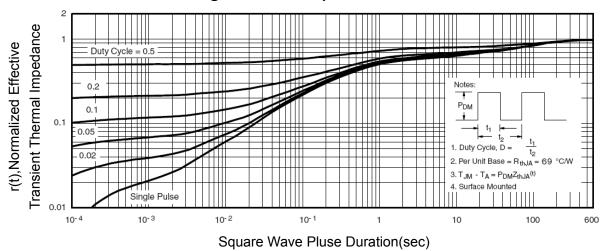
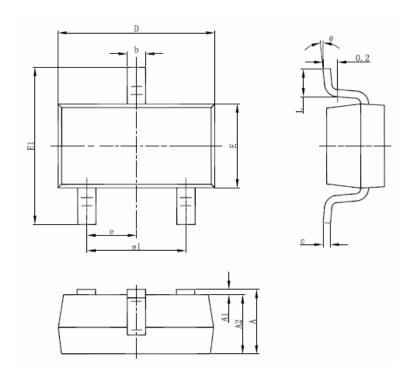


Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23-3L Package Information



Symbol	Dimensions Ir	Millimeters	Dimensions	In Inches	
Symbol	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ± 0.10 mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- $5. \ Controlling \ dimension \ is \ millimeter, \ converted \ inch \ dimensions \ are \ not \ necessarily \ exact.$



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